





CDC3RL02 SCHS371G - NOVEMBER 2009 - REVISED NOVEMBER 2022

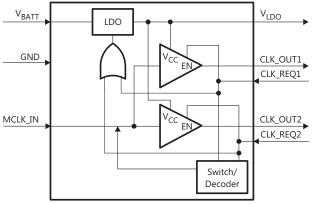
CDC3RL02 Low Phase-Noise Two-Channel Clock Fan-Out Buffer

1 Features

- Low Additive Noise:
 - 149 dBc/Hz at 10-kHz Offset Phase Noise
 - 0.37 ps (RMS) Output Jitter
- Limited Output Slew Rate for EMI Reduction (1- to 5-ns Rise/Fall Time for 10-pF to 50-pF Loads)
- Adaptive Output Stage Controls Reflection
- Regulated 1.8-V Externally Available I/O Supply
- Ultra-Small 8-bump YFP 0.4-mm Pitch WCSP $(0.8 \text{ mm} \times 1.6 \text{ mm})$
- ESD Performance Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 1000-V Charged-Device Model (JESD22-C101-A Level III)

2 Applications

- Cellular Phones
- Global Positioning Systems (GPS)
- Wireless LAN
- FM Radio
- WiMAX
- W-BT



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Simplified Block Diagram

3 Description

The CDC3RL02 is a two-channel clock fan-out buffer and is ideal for use in portable end-equipment, such as mobile phones, that require clock buffering with minimal additive phase noise and fan-out capabilities. It buffers a single master clock, such as a temperature compensated crystal oscillator (TCXO) to multiple peripherals. The device has two clock request inputs (CLK_REQ1 and CLK_REQ2), each of which enable a single clock output.

The CDC3RL02 accepts square or sine waves at the master clock input (MCLK IN), eliminating the need for an AC coupling capacitor. The smallest acceptable sine wave is a 0.3-V signal (peak-topeak). CDC3RL02 has been designed to offer minimal channel-to-channel skew, additive output jitter, and additive phase noise. The adaptive clock output buffers offer controlled slew-rate over a wide capacitive loading range which minimizes EMI emissions, maintains signal integrity, and minimizes ringing caused by signal reflections on the clock distribution lines.

The CDC3RL02 has an integrated Low-Drop-Out (LDO) voltage regulator which accepts input voltages from 2.3 V to 5.5 V and outputs 1.8 V, 50 mA. This 1.8-V supply is externally available to provide regulated power to peripheral devices such as a TCXO.

The CDC3RL02 is offered in a 0.4-mm pitch waferlevel chip-scale (WCSP) package (0.8 mm × 1.6 mm) and is optimized for very low standby current consumption.

Device Information

PART NUMBER (1)	PACKAGE	BODY SIZE (NOM)
CDC3RL02	DSBGA (8)	0.80 mm × 1.60 mm

For all available packages, see the orderable addendum at the end of the data sheet.



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•	• • •	Layout sections to the Application and Implement	
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-	Changed MCLK IN frequency maximum value from	om: 52 MHz to: 54 MHz	<u></u>
	Changed Mock_in frequency maximum value in	311. 32 Wil 12 to. 34 Wil 12	
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5 Device Comparison

Table 5-1. Device Comparison

T _A	PACKAGE (1)	ORDERABLE PART NUMBER	BACKSIDE COATING (2)
-40 C to 85 C	YFP	CDC3RL02BYFPR	Yes
-40 C to 85 C	YFP	CDC3RL02YFPR	No

⁽¹⁾ Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

6 Pin Configuration and Functions

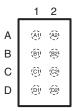


Figure 6-1. YFP Package 8-Pin DSBGA Top View

Table 6-1. Pin Functions

PIN		I/O	DESCRIPTION	
NAME	NO.	1/0	DESCRIPTION	
V _{BATT}	A1	I	Input to internal LDO	
CLK_OUT1	A2	0	Clock output 1	
V_{LDO}	B1	0	1.8 V I/O supply for CDC3RL02 and external TCXO	
CLK_REQ1	B2	I	Clock request 1 (from peripheral) for Clock output 1	
MCLK_IN	C1	I	Master clock input	
CLK_REQ2	C2	I	Clock request 2 (from peripheral) for Clock output 2	
GND	D1	_	Ground	
CLK_OUT2	D2	0	Clock output 2	

Table 6-2. YFP Package Pin Assignments

	1	2
Α	V_{BATT}	CLK_OUT1
В	V_{LDO}	CLK_REQ1
С	MCLK_LIN	CLK_REQ2
D	GND	CLK_OUT2

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²⁾ CSP (DSBGA) devices manufactured with backside coating have an increased resistance to cracking due to the increased physical strength of the package. Devices with backside coating are highly encouraged for new designs.



7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range, unless otherwise noted. (1)

			MIN	MAX	UNIT
V _{BATT}	Voltage range ⁽²⁾		-0.3	7	V
	Voltage range(3)	CLK_REQ_1/2, MCLK_IN	-0.3	V _{BATT} + 0.3	V
Voltage range ⁽³⁾		V _{LDO} , CLK_OUT_1/2 ⁽²⁾	-0.3	V _{BATT} + 0.3	
I _{IK}	Input clamp current at V _{BATT} , CLK_REQ_1/2, and MCLK_IN	V ₁ < 0		-50	mA
Io	Continuous output current	CLK_OUT1/2		±20	mA
	Continuous current through GND, V _{BAT}	rt, V _{LDO}		±50	mA
TJ	Operating virtual junction temperature		-40	150	°C
T _A	Operating ambient temperature range		-40	85	°C
T _{stg}	Storage temperature range		-55	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- (2) The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) All voltage values are with respect to network ground pin.

7.2 ESD Ratings

			VALUE	UNIT
		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000	V
		Machine Model	200	

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 500-V HBM is possible with the necessary precautions.

7.3 Recommended Operating Conditions

See (1)

			MIN	MAX	UNIT
V _{BATT}	Input voltage to internal LDO		2.3	5.5	V
VI	Input voltage	MCLK_IN, CLK_REQ1/2	0	1.89	V
Vo	Output voltage	CLK_OUT1/2	0	1.8	V
V _{IH}	High-level input voltage	CLK_REQ1/2	1.3	1.89	V
V _{IL}	Low-level input voltage	CLK_REQ1/2	0	0.5	V
I _{OH}	High-level output current, DC current		-8		mA
I _{OL}	Low-level output current, DC current			8	mA

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. See the TI application report, *Implications of Slow or Floating CMOS Inputs*, SCBA004.

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⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 250-V CDM is possible with the necessary precautions.



7.4 Thermal Information

		CDC3RL02	
THERMAL METRIC(1)		YFP (TSSOP)	UNIT
		8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	107.8	°C/W
R ₀ JC(top)	Junction-to-case (top) thermal resistance	1.3	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	18.1	°C/W
ΨЈТ	Junction-to-top characterization parameter	4.5	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	18.1	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report (SPRA953).

7.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

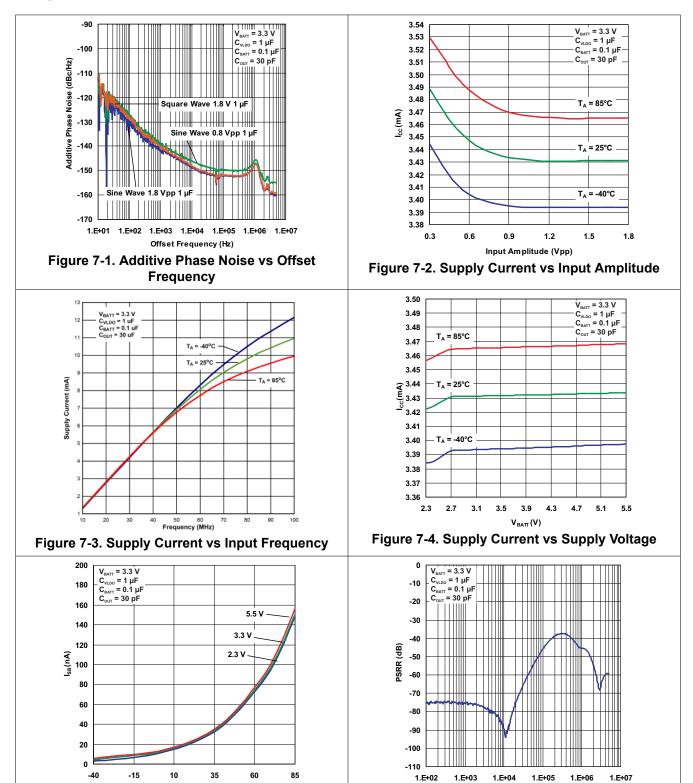
PARAMETER		TEST CONI	DITIONS	MIN	TYP	MAX	UNIT	
LDO								
V _{OUT}	LDO output voltage	I _{OUT} = 50 mA		1.71	1.8	1.89	V	
C _{LDO}	External load capacitance			1		10	μF	
I _{OUT(SC)}	Short circuit output current	R _L = 0 Ω	$R_L = 0 \Omega$		100		mA	
I _{OUT(PK)}	Peak output current	V _{BATT} = 2.3 V, V _{LDO} = V _{OUT} - 5	V _{BATT} = 2.3 V, V _{LDO} = V _{OUT} – 5%			100	mA	
PSR	Dower cumply rejection	\/ - 2.2.\/ - 2.m/	f _{IN} = 217 Hz and 1 kHz	60			dB	
PSK	Power supply rejection	V_{BATT} = 2.3 V, I_{OUT} = 2 mA,	f _{IN} = 3.25 MHz	40			uБ	
	LDO startup time	V_{BATT} = 2.3 V , C_{LDO} = 1 μ F, CLK_REQ_n to V_{IH} = 1.71 V			0.2		ma	
t _{su}	LDO startup time	V_{BATT} = 5.5 V , C_{LDO} = 10 μ F, CLK_REQ_n to V_{IH} = 1.71 V				1	ms	
POWER	CONSUMPTION							
I _{SB}	Standby current	Device in standby (all V _{CLK_RE}	_{Q_n} = 0 V)		0.2	1	μA	
I _{CCS}	Static current consumption	Device active but not switching	3		0.4	1	mA	
I _{OB}	Output buffer average current	f _{IN} = 26 MHz, C _{LOAD} = 50 pF			4.2		mA	
C _{PD}	Output power dissipation capacitance	f _{IN} = 26 MHz				44	pF	
MCLK_I	N INPUT	1						
II	MCLK_IN, CLK_REQ_1/2 leakage current	V _I = V _{IH} or GND				1	μΑ	
Cı	MCLK_IN capacitance	f _{IN} = 26 MHz			4.75		pF	
R _I	MCLK_IN impedance	f _{IN} = 26 MHz			6		kΩ	
f _{IN}	MCLK_IN frequency range			10	26	80	MHz	
MCLK_I	N LVCMOS SOURCE							
			1-kHz offset		-140			
	Additive phase noise	$ f_{IN} = 26 \text{ MHz}, t_r/t_f \le 1 \text{ ns}$	10-kHz offset		-149		dBc/Hz	
	Additive phase noise	11N - 20 IVITIZ, L ₁ /L ₁ = 1 115	100-kHz offset		-153		ubc/nz	
			1-MHz offset		-148			
	Additive jitter	f _{IN} = 26 MHz, V _{PP} = 0.8 V, BW	= 10–5 MHz		0.37		ps (rms)	
t _{DL}	MCLK_IN to CLK_OUT_n propagation delay				11		ns	
DCL	Output duty cycle	f _{IN} = 26 MHz, DC _{IN} = 50%		45%	50%	55%		

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CON	DITIONS	MIN	TYP	MAX	UNIT	
MCLK	IN SINUSOIDAL SOURCE			<u> </u>				
V_{MA}	Input amplitude			0.3		1.8	V	
			1-kHz offset		-141			
		f - 26 MHz \/ - 1.8 \/	10-kHz offset		-149			
	Additive phase noise	$f_{IN} = 26 \text{ MHz}, V_{MA} = 1.8 V_{PP}$	100-kHz offset		-152			
			1-MHz offset		-148		4D - / L	
			1-kHz offset		-139		dBc/Hz	
		f - 00 MH - 1/ - 0.01/	10-kHz offset		-146			
			100-kHz offset		-150			
			1-MHz offset		-146			
	Additive jitter	f _{IN} = 26 MHz, V _{MA} = 1.8 V _{PP} , I	3W = 10–5 MHz		0.41		ps (RMS)	
t _{DS}	MCLK_IN to CLK_OUT_1/2 propagation delay				12		ns	
DCs	Output duty cycle	f _{IN} = 26 MHz, V _{MA} > 1.8 V _{PP}		45%	50%	55%		
CLK_C	OUT_N OUTPUTS			•				
t _r	20% to 80% rise time	C _L = 10 pF to 50 pF		1		5.2	ns	
t _f	20% to 80% fall time	C _L = 10 pF to 50 pF		1		5.2	ns	
t _{sk}	Channel-to-channel skew	$C_L = 10 \text{ pF to } 50 \text{ pF } (C_{L1} = C_L)$	2)	-0.5		0.5	ns	
V	Lligh lavel output voltage	I_{OH} = -100 μ A, reference to V	$I_{OH} = -100 \mu A$, reference to V_{LDO}				V	
V _{OH} High-level output voltage		I _{OH} = -8 mA	I _{OH} = -8 mA				V	
V	Low level output voltage	I _{OL} = 20 μA				0.2	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
V _{OL}	Low-level output voltage	I _{OL} = 8 mA				0.55	V	



7.6 Typical Characteristics



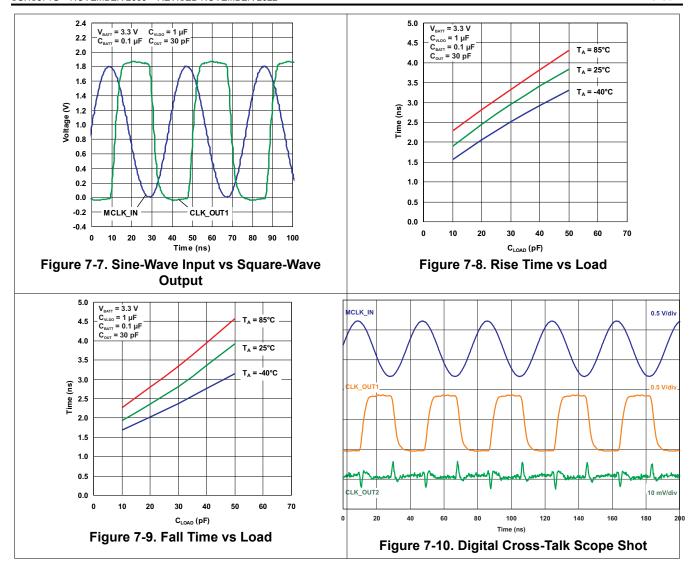
Temperature (°C)

Figure 7-5. Standby Current vs Temperature

Figure 7-6. Power Supply Rejection vs Input

Frequency





8 Detailed Description

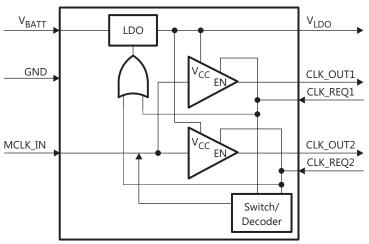
8.1 Overview

The CDC3RL02 is a two-channel clock fan-out buffer and is ideal for use in portable end-equipment, such as mobile phones, that require clock buffering with minimal additive phase noise and fan-out capabilities. It buffers a single master clock, such as a temperature compensated crystal oscillator (TCXO) to multiple peripherals. The device has two clock request inputs (CLK_REQ1 and CLK_REQ2), each of which enable a single clock output.

The CDC3RL02 accepts square or sine waves at the master clock input (MCLK_IN), eliminating the need for an AC coupling capacitor. The smallest acceptable sine wave is a 0.3-V signal (peak-to-peak). CDC3RL02 has been designed to offer minimal channel-to-channel skew, additive output jitter, and additive phase noise. The adaptive clock output buffers offer controlled slew-rate over a wide capacitive loading range which minimizes EMI emissions, maintains signal integrity, and minimizes ringing caused by signal reflections on the clock distribution lines.

The CDC3RL02 has an integrated Low-Drop-Out (LDO) voltage regulator which accepts input voltages from 2.3 V to 5.5 V and outputs 1.8 V, 50 mA. This 1.8-V supply is externally available to provide regulated power to peripheral devices such as a TCXO.

8.2 Functional Block Diagram



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8.3 Feature Description

8.3.1 Low Additive Noise

The CDC3RL02 features –149 dBc/Hz at 10 kHz offset phase noise and 0.37 ps (RMS) of output jitter, to make sure that the buffered signals are clean.

8.3.2 Regulated 1.8-V Externally Available I/O Supply

The CDC3RL02 allows users to connect to the output of the internal LDO, for providing power to other ICs. For more information, refer to *LDO*.

8.3.3 Ultra-Small 8-bump YFP 0.4-mm Pitch WCSP Package

Using the ultra-small YFP package, the CDC3RL02 is very small and allows it to be placed on a board with minimum work.



8.4 Device Functional Modes

Table 8-1 is the function table for CDC3RL02.

Table 8-1. Function Table

	INPUTS	OUTPUTS		
CLK_REQ1 ⁽¹⁾	CLK_REQ2 ⁽¹⁾	MCLK_IN	CLK_OUT1	CLK_OUT2
L	L	X	L	L
L	Н	CLK	L	CLK
Н	L	CLK	CLK	L
Н	Н	CLK	CLK	CLK

⁽¹⁾ If a CLK_OUT will always be enabled, it is acceptable to tie its CLK_REQ pin to an external 1.8 V source (not VLDO).

9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

9.1.1 Input Clock Squarer

Figure 9-1 shows the input stage of the CDC3RL02. The input signal at MCLK_IN can be a square wave or sine wave. C_{MCLK} is an internal AC coupling capacitor that allows a direct connection from the TCXO to the CDC3RL02 without an external capacitor.

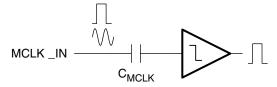


Figure 9-1. Input Stage with Internal AC Coupling Capacitor

Any external component added in the series path of the clock signal will potentially add phase noise and jitter. The error source associated with the internal decoupling capacitor is included in the specification of the CDC3RL02. The recommended clock frequency band of the CDC3RL02 is 10 MHz to 80 MHz for specified functionality. All performance metrics are specified at 26 MHz. The lowest acceptable sinusoidal signal amplitude is $0.8~V_{PP}$ for specified performance. Amplitudes as low as $0.3~V_{PP}$ are acceptable but with reduced phase-noise and jitter performance.

9.1.2 Output Stage

Each output drives 1.8-V LVCMOS levels. Adaptive output buffers limit the rise/fall time of the output to within 1 ns to 5 ns with load capacitance between 10 pF and 50 pF. Fast slew rates introduce EMI into the system. Each output buffer limits EMI by keeping the rise/fall time above 1 ns. Slow rise/fall times can induce additive phase noise and duty cycle errors in the load device. The output buffer limits these errors by keeping the rise/fall time below 5 ns. In addition, the output stage dynamically alters impedance based on the instantaneous voltage level of the output. This dynamic change limits reflections keeping the output signal monotonic during transitions. Each output is active low when not requested to avoid false clocking of the load device.

9.1.3 LDO

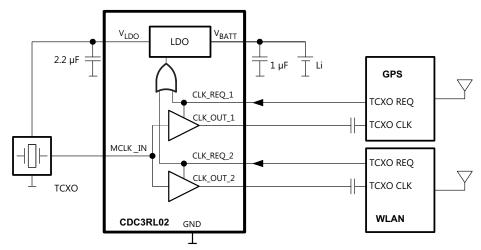
A low noise 1.8-V LDO is integrated to provide the I/O supply for the output buffers. The LDO output is externally available to power a clock source such as a TCXO. A clean supply is provided to the clock buffers and the clock source for optimum phase noise performance. The input range of the LDO allows the device to be powered directly from a single cell Li battery. The LDO is enabled by either of the CLK_REQ_N signals. When disabled, the device enters a low power shutdown mode consuming less than 1 μ A from the battery. The LDO requires an output decoupling capacitor in the range of 1 μ F to 10 μ F with an equivalent series resistance (ESR) of at least 0.1 Ω for compensation and high-frequency PSR. This capacitor must stay within the specified range for capacitance and ESR over the entire operating temperature range. A ceramic capacitor can be used if a small external resistance is added in series with it to increase the effective ESR. An input bypass capacitor of 1 μ F or larger is recommended.

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9.2 Typical Application

The CDC3RL02 is ideal for use in mobile applications as shown in Figure 9-2. In this example, a single low noise TCXO system clock source is buffered to drive a mobile GPS receiver and WLAN transceiver. Each peripheral independently requests an active clock by asserting a single clock request line (CLK_REQ_1 or CLK_REQ_2). When both clock request lines are inactive, the CDC3RL02 enters a low current shutdown mode. In this mode, the LDO output, CLK_OUT_1, and CLK_OUT_2 are pulled to GND and the TCXO will be unpowered.



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Figure 9-2. Mobile Application

When either peripheral requests the clock, the CDC3RL02 will enable the LDO and power the TCXO. The TCXO output (square wave, sine wave, or clipped sine wave) is converted to a square wave and buffered to the requested output.

9.2.1 Design Requirements

For the typical application, the user must know the following parameters.

Table 9-1. Design Parameters

PARAMETER	DESCRIPTION	EXAMPLE VALUE
V _{BATT}	Input voltage from battery or power supply	3.7 V
MCLK_IN	Input frequency from a TCXO	26 MHz

9.2.2 Detailed Design Procedure

The designer must make sure that all parameters are within the ranges specified in *Recommended Operating Conditions*.

Each device which receives a clock output from the CDC3RL02 should have the CLK request pin connected to the appropriate CLK_REQ pin on the CDC3RL02. This will enable the output buffer when a device requests the clock signal.

It is possible to have a control the outputs of the clock by using a GPIO from a controller to control the CLK_REQ pins.

If one of the outputs is unused, then tie the CLK_REQ and CLK_OUT pins to ground. If the user wants a CLK_OUT pin always enabled, it is acceptable to tie the paired CLK_REQ pin to an external 1.8-V source (not V_{LDO} because the LDO output is not enabled until at least one CLK_REQ pin is high).

9.2.3 Application Curve

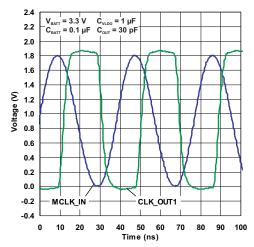


Figure 9-3. Sine Wave Input vs Output

9.3 Power Supply Recommendations

General power supply recommendations are to be considered for the CDC3RL02. These include:

- Decoupling capacitors placed close to the V_{BATT} pin of typical values (1 μ F)
- V_{BATT} be within the recommended voltage range

9.4 Layout

9.4.1 Layout Guidelines

To ensure reliability of the device, following common printed-circuit board layout guidelines is recommended.

- Bypass capacitors should be used on power supplies and should be placed as close as possible to the V_{BATT} pin
- · Short trace-lengths should be used to avoid excessive loading
- For improved performance on the clock output lines, use a ground trace on the sides of the clock trace to minimize crosstalk and EMI

9.4.2 Layout Example

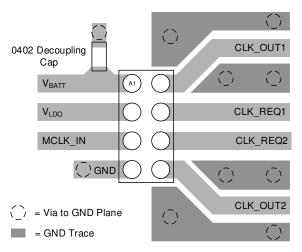


Figure 9-4. Example Layout for YFP Package



10 Device and Documentation Support

10.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

10.2 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

10.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

10.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

10.5 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
CDC3RL02BYFPR	ACTIVE	DSBGA	YFP	8	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	4LN	Samples
CDC3RL02YFPR	ACTIVE	DSBGA	YFP	8	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	4LN	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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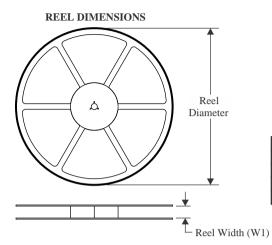
PACKAGE OPTION ADDENDUM

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

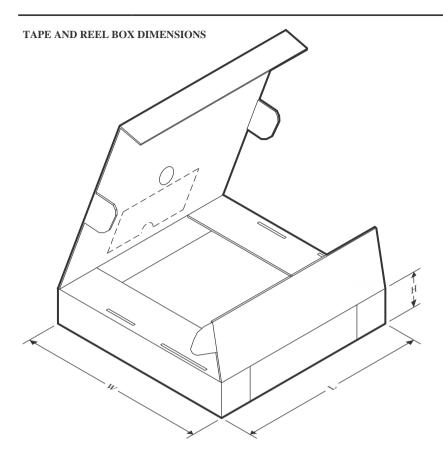
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	U	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CDC3RL02YFPR	DSBGA	YFP	8	3000	178.0	9.2	0.9	1.75	0.6	4.0	8.0	Q1

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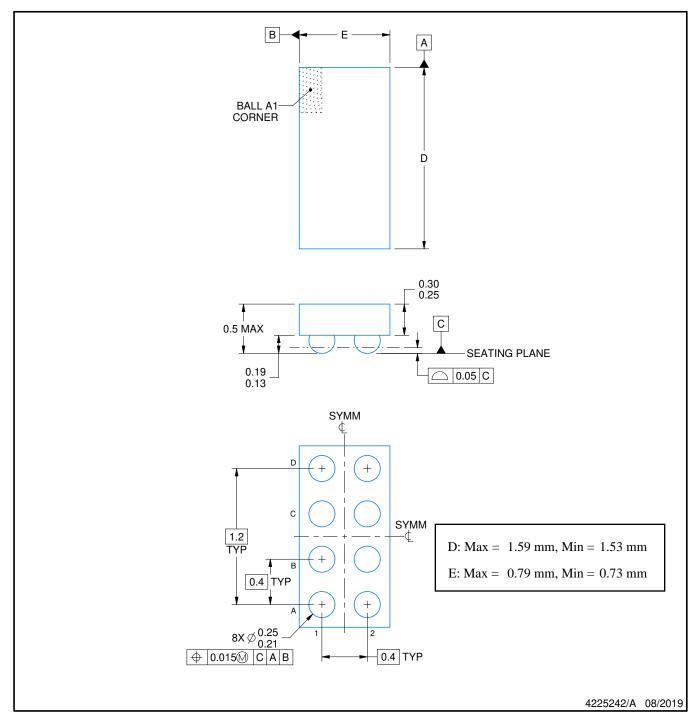


*All dimensions are nominal

Device	Device Package Type		Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
CDC3RL02YFPR	DSBGA	YFP	8	3000	220.0	220.0	35.0	



DIE SIZE BALL GRID ARRAY



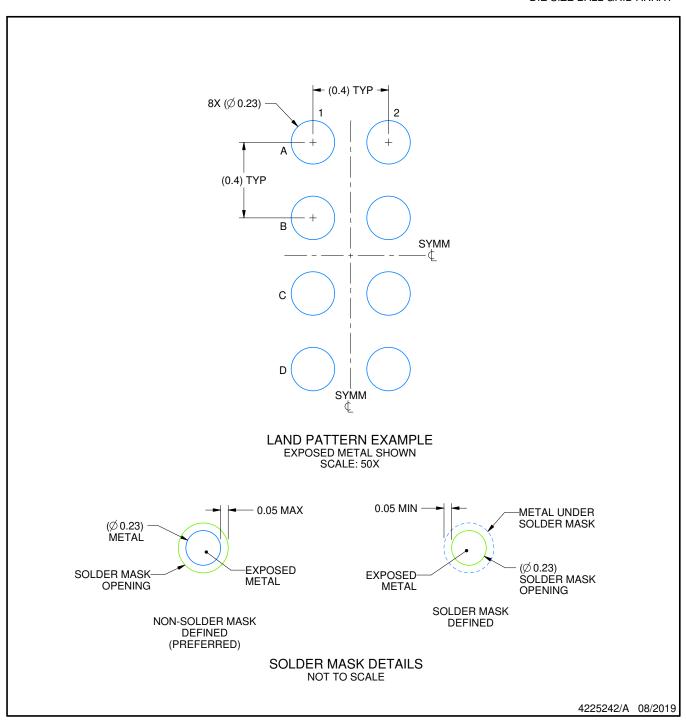
NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.



DIE SIZE BALL GRID ARRAY

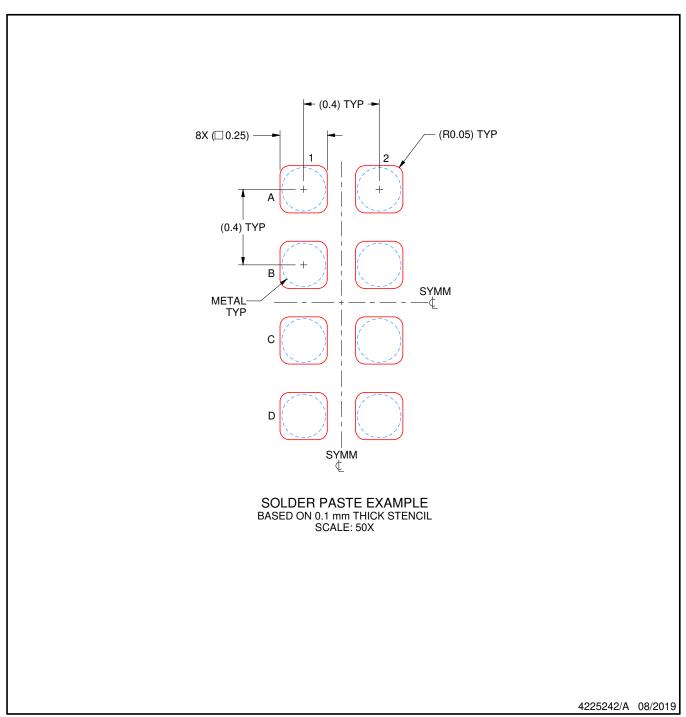


NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. See Texas Instruments Literature No. SNVA009 (www.ti.com/lit/snva009).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



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